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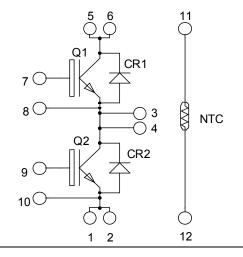
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Phase leg High speed IGBT 5 Power Module

$V_{CES} = 650V$ $I_{C} = 100A$ @ Tc = 25°C



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- High speed IGBT 5
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 100 kHz
 - Low leakage current
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

All ratings (a) $T_i = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings (Per IGBT)

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Voltage		650	V
т	Continuous Collector Current	$\Gamma_{\rm C} = 25^{\circ}{\rm C}$	100	
I _C	Continuous Collector Current $T_c = 80^{\circ}C$		60	Α
I _{CM}	Pulsed Collector Current	$\Gamma_{\rm C} = 25^{\circ}{\rm C}$	200	
V _{GE}	Gate – Emitter Voltage		± 20	V
PD	Power Dissipation		250	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APTGTQ100A65T1G-Rev 1 January, 2017



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Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 650V$				100	μΑ
V _{CE(sat)}	Collector Emitter Saturation Voltage	, GE 10 ,	$T_j = 25^{\circ}C$		1.65	2.2	V
			$T_{j} = 150^{\circ}C$		1.9		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1mA$		3.3	4.0	4.7	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				240	nA

Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			6000	-	
C _{oes}	Output Capacitance				100		pF
Cres	Reverse Transfer Capacitance	f = 1 MHz		22			
Q _G	Gate charge	$V_{GE} = 15V, I_C = 100A$ $V_{CE} = 520V$			240		nC
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)			21		
Tr	Rise Time	$V_{GE} = 15V$			15		ns
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 400V$ $I_C = 50A$			180		
$T_{\rm f}$	Fall Time	$R_{\rm G} = 2\Omega$			18		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = 15V$ $V_{Bus} = 400V$ $I_C = 50A$ $R_G = 2\Omega$			20		
Tr	Rise Time				15		
T _{d(off)}	Turn-off Delay Time				205		ns
$T_{\rm f}$	Fall Time				26		
Eon	Turn on Energy	$V_{GE} = 15V$ $V_{Bus} = 400V$ $I_C = 50A$ $R_G = 2\Omega$	$T_{j} = 150^{\circ}C$		1.5		mJ
E _{off}	Turn off Energy		$T_{j} = 150^{\circ}C$		0.6		111,0
R _{Gint}	Integrated gate resistor				2.5		Ω
R _{thJC}	Junction to Case Thermal Resistance					0.6	°C/W

Diode ratings and characteristics (per diode)

Symbol	Characteristic	cteristic Test Conditions		Min	Тур	Max	Unit		
V _{RRM}	Peak Repetitive Reverse Voltage					650	V		
I _{RM}	Reverse Leakage Current	V _R =650V				100	μA		
I _F	DC Forward Current		$Tc = 25^{\circ}C$		100		А		
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 100 \text{A}$ $V_{\rm GE} = 0 \text{V}$	$T_i = 25^{\circ}C$		1.6	2.2	V		
		$V_{GE} = 0V$	$T_i = 150^{\circ}C$		1.65		v		
t	t_{rr} Reverse Recovery Time $I_F = 50A$ $V_R = 400V$	$T_j = 25^{\circ}C$		46		ns			
ι _{rr}		$\begin{bmatrix} I_F = 50A \\ V_f = 400V \end{bmatrix} = \begin{bmatrix} T_j = 1 \end{bmatrix}$	$T_{j} = 150^{\circ}C$		62		115		
0	Reverse Recovery Charge	di/dt = 2000 A		di/dt = 2000 A/ug	$T_j = 25^{\circ}C$		1		
Q _{rr}			$T_{j} = 150^{\circ}C$		2		μC		
R _{thJC}	Junction to Case Thermal Resistance					0.7	°C/W		



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Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

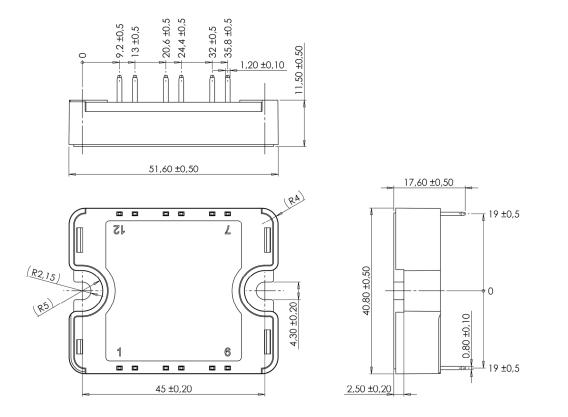
Symbol	Characteristic	,	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		T _C =100°C		4		%
	D					

 $R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$ T: Thermistor temperature R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz					V
T _J	Operating junction temperature range			-40	175	
T _{JOP}	Recommended junction temperature under switching conditions			-40	T _J max -25	°C
T _{STG}	Storage Temperature Range			-40	125	C
T _C	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				80	g

Package outline (dimensions in mm)

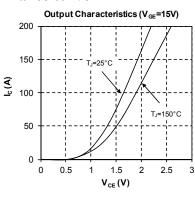


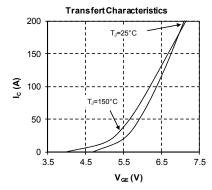
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

www.microsemi.com

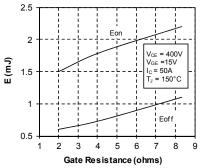


Typical performance curve

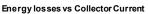


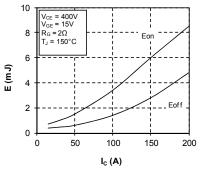


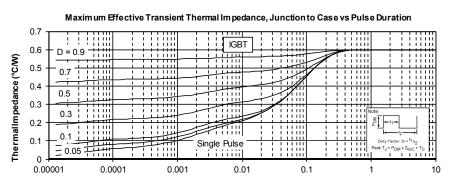
Switching Energy Losses vs Gate Resistance



Output Characteristics 200 T_J = 150°C 150 V_{GE}=20\ I_c (A) VGE=8 V_{GE}=15V 100 V_{GE}=13V 50 0 0.5 0 1.5 2.5 3 3.5 1 2 4 V_{CE} (V)



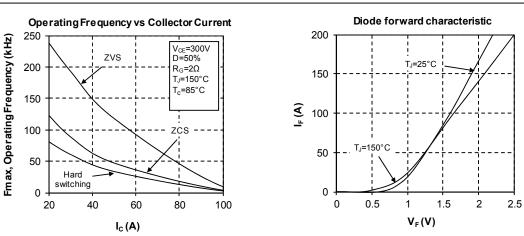


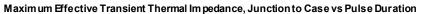


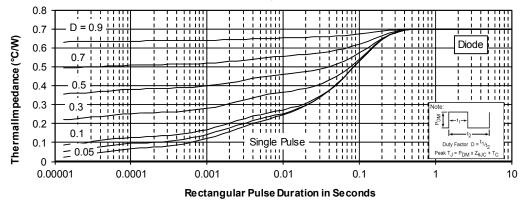
Rectangular Pulse Duration in Seconds

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